

DC Low Current Input 4-Pin Phototransistor Optocoupler

Features

- High isolation 5000 VRMS
- CTR flexibility available see order information
- DC input with transistor output
- External Creepage ≥ 7.5mm (S/SL Type)
- External Creepage ≥ 8.0mm (SLM Type)
- Operating temperature range 55 ℃ to 110 ℃
- RoHS compliance
- REACH compliance
- Halogen compliance (Optional)
- Regulatory Approvals
 - UL UL1577 (E364000)
 - VDE EN60747-5-5(VDE0884-5)
 - CQC GB4943.1, GB8898
 - IEC60065, IEC60950

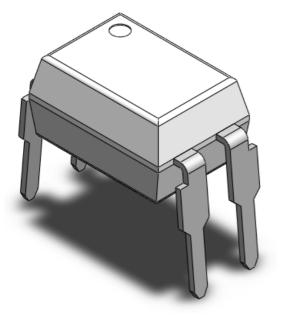
Description

The CT816L series consists of a photo transistor optically coupled to a gallium arsenide Infrared-emitting diode in a 4-lead DIP package different lead forming options.

Applications

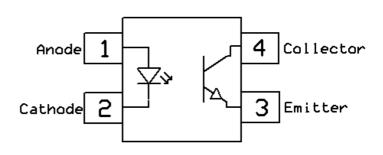
- Switch mode power supplies
- Computer peripheral interface
- Microprocessor system interface

Package Outline



Note: Different lead forming options available. See package dimension.

Schematic





DC Low Current Input 4-Pin Phototransistor Optocoupler

Absolute Maximum Rating at 25°C

Symbol	Parameters	Ratings	Units	Notes
Viso	Isolation voltage	5000	V _{RMS}	
Ртот	Total power dissipation	200	mW	
Topr	Operating temperature	-55 ~ +110	°C	
Тsтg	Storage temperature	-55 ~ +150	۰C	
Tsol	Soldering temperature	260	۰C	
Emitter		·		
l _F	Forward current	60	mA	
I _{F(TRANS)}	Peak transient current (≤1µs P.W,300pps)	1	Α	
V _R	Reverse voltage	6	V	
PD	Emitter power dissipation	100	mW	
Detector		·		
PD	Detector power dissipation	150	mW	
Вусео	Collector-Emitter Breakdown Voltage	80	V	
Bveco	Emitter-Collector Breakdown Voltage	7	V	
Ic	Collector Current	50	mA	



DC Low Current Input 4-Pin Phototransistor Optocoupler

Electrical Characteristics $T_A = 25 \, ^{\circ}\text{C}$ (unless otherwise specified)

Emitter Characteristics

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
VF	Forward voltage	I _F =1mA		1.3	1.4	٧	
IR	Reverse Current	V _R = 6V	-	-	5	μΑ	
C _{IN}	Input Capacitance	f= 1MHz	-	15	-	pF	

Detector Characteristics

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
Bvceo	Collector-Emitter Breakdown	I _C = 100μA	80	-	-	٧	
Bveco	Emitter-Collector Breakdown	I _E = 100μA	7	-	-	٧	
ICEO	Collector-Emitter Dark Current	V _{CE} = 20V, I _F =0mA	-	-	100	nA	

Transfer Characteristics

Symbol	Parameters	;	Test Conditions	Min	Тур	Max	Units	Notes
	Current Transfer Ratio	CT816L2	I _F = 1mA, V _{CE} = 0.5V	63	-	125	- %	
CTR		CT816L3		100	-	200		
CIN		CT816L4	F= IIIIA, VCE= 0.3V	160	1	320	70	
		CT816L5		250	1	500		
	Current Transfer Ratio -	CT816L2	IF= 0.5mA, V _{CE} = 1.5V	32	75	-	%	
CTD		CT816L3		50	120	-		
CTR		CT816L4		80	200	-		
		CT816L5		125	300	-		
		CT816L2	I _F = 1mA, I _C = 0.32mA	-	0.2	0.4		
\/	Collector-Emitter	tter CT816L3 I _F = 1mA, I _C = 0.50mA	I _F = 1mA, I _C = 0.50mA	-	0.2	0.4	V	
V _{CE(SAT)}	Saturation Voltage	CT816L4	I _F = 1mA, I _C = 0.80mA	-	0.2	0.4	V	
		CT816L5	I _F = 1mA, I _C = 1.25mA	-	0.2	0.4		
Rio	Isolation Resistance		V _{IO} = 500V _{DC}	5x10 ¹⁰	-	-	Ω	
Cıo	Isolation Capacitance		f= 1MHz	-	0.25	1	pF	

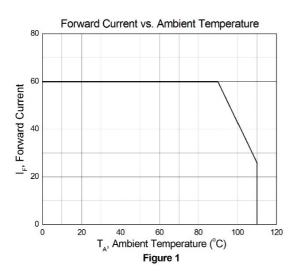


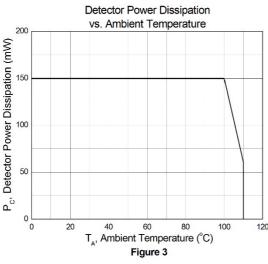
DC Low Current Input 4-Pin Phototransistor Optocoupler

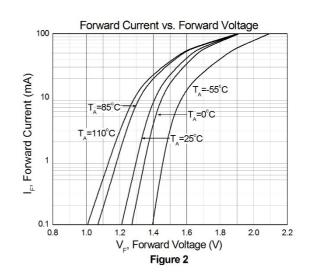
Switching Characteristics

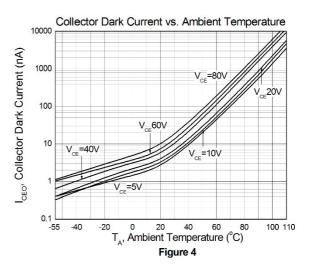
Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
tr	Rise Time		-	4.9	-		
t _f	Fall Time	I _C = 2mA, V _{CC} = 5V,	-	6.5	-	0	
t _{on}	Turn-on Time	R _L = 100Ω	-	8.6	-	μS	
t _{off}	Turn-off Time		-	6.9	-		

Typical Characteristic Curves





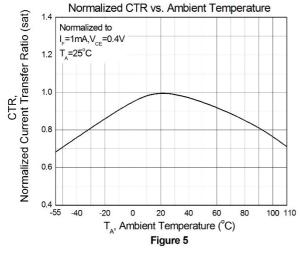


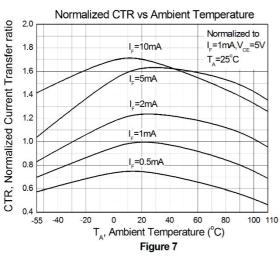


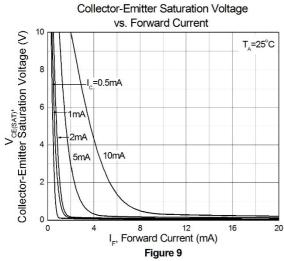


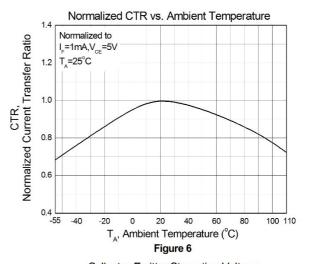


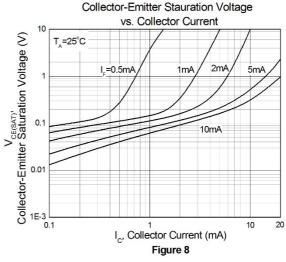
Typical Characteristic Curves

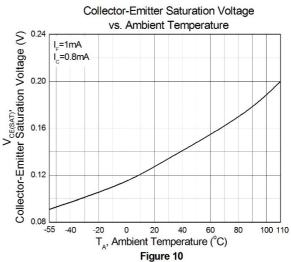






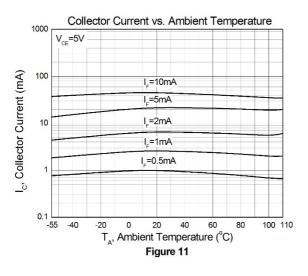


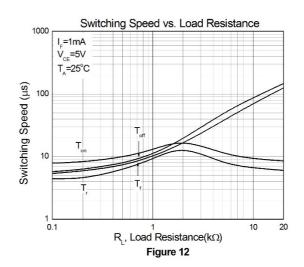


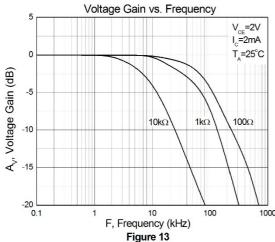




Typical Characteristic Curves







Test Circuit

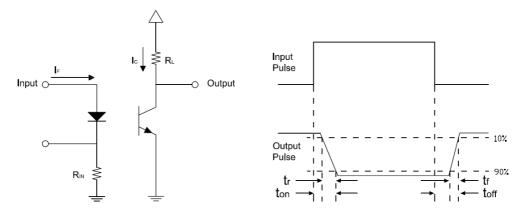


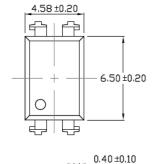
Figure 14: Switching Time Test Circuits

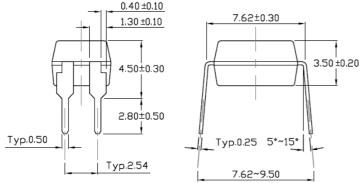




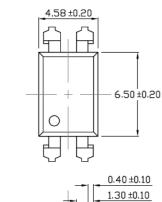
Package Dimension Dimensions in mm unless otherwise stated

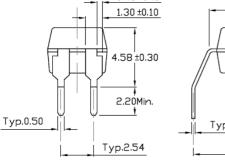
Standard DIP - Through Hole

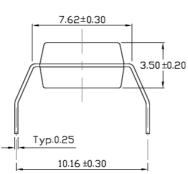




Gullwing (400mil) Lead Forming – Through Hole (M Type)



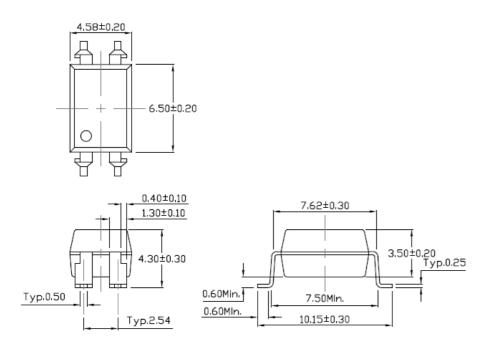




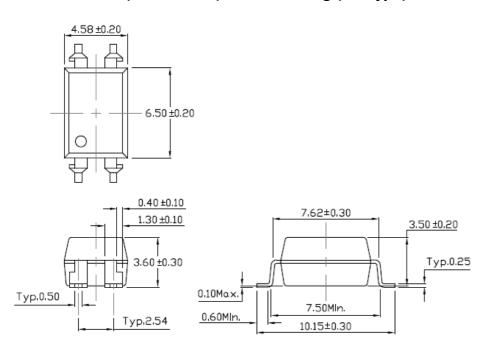




Surface Mount Lead Forming (S Type)



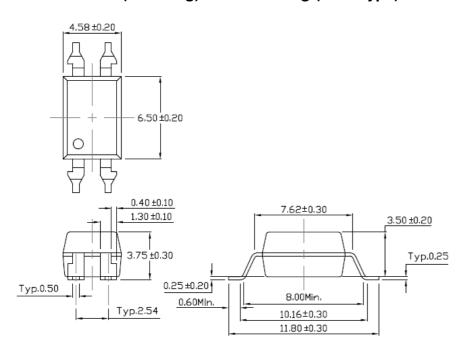
Surface Mount (Low Profile) Lead Forming (SL Type)







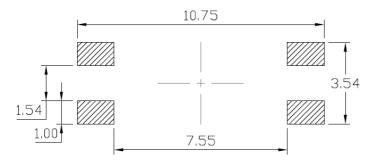
Surface Mount (Gullwing) Lead Forming (SLM Type)



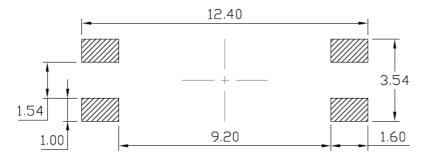


Recommended Solder Mask Dimensions in mm unless otherwise stated

Surface Mount Lead Forming & Surface Mount (Low Profile) Lead Forming



Surface Mount (Gullwing) Lead Forming



Marking Information



Note:

CT : Denotes "CT Micro"

816L : Part NumberR : CTR RankV : VDE OptionY : Fiscal YearWW : Work Week

K : Manufacturing Code





Ordering Information

CT816LX(V)(Y)(Z)-G

X = Part No. (X = 2, 3, 4, 5 or None)

Y = Lead form option (S, SL, M, SLM or none)

Z = Tape and reel option (T1, T2, T3, T4 or none)

G= Material option (G: Green, None: Non-green)

Option	Description	Quantity
None	Standard 4 Pin Dip	100 Units/Tube
М	Gullwing (400mil) Lead Forming	100 Units/Tube
S(T1)	Surface Mount Lead Forming – With Option 1 Taping	1500 Units/Reel
S(T2)	Surface Mount Lead Forming – With Option 2 Taping	1500 Units/Reel
S(T3)	Surface Mount Lead Forming – With Option 3 Taping	1000 Units/Reel
S(T4)	Surface Mount Lead Forming – With Option 4 Taping	1000 Units/Reel
SL(T1)	Surface Mount (Low Profile) Lead Forming- With Option 1 Taping	1500 Units/Reel
SL(T2)	Surface Mount (Low Profile) Lead Forming – With Option 2 Taping	1500 Units/Reel
SL(T3)	Surface Mount (Low Profile) Lead Forming- With Option 3 Taping	1000 Units/Reel
SL(T4)	Surface Mount (Low Profile) Lead Forming – With Option 4 Taping	1000 Units/Reel
SLM(T1)	Surface Mount (Gullwing) Lead Forming- With Option 1 Taping	1500 Units/Reel
SLM(T2)	Surface Mount (Gullwing) Lead Forming – With Option 2 Taping	1500 Units/Reel

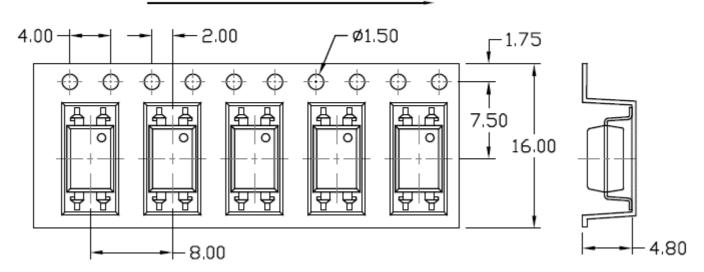




Carrier Tape Specifications Dimensions in mm unless otherwise stated

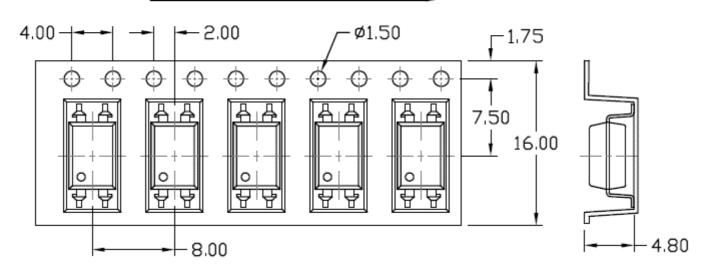
Option S(T1) & SL(T1)

Input Direction



Option S(T2) & SL(T2)

Input Direction

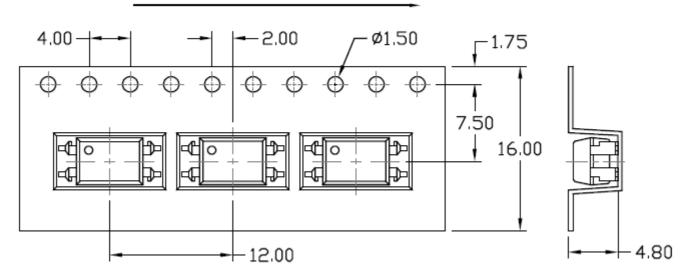






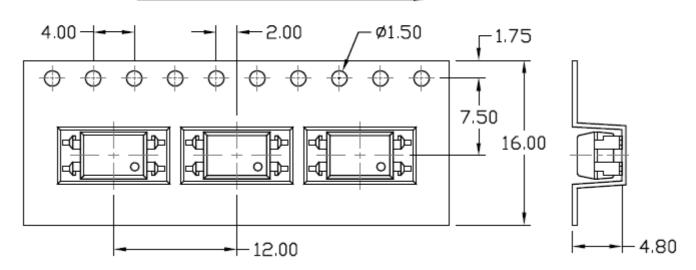
Option S(T3) & SL(T3)

Input Direction



Option S(T4) & SL(T4)

Input Direction

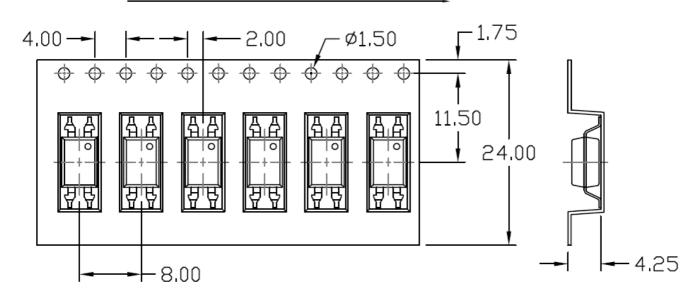






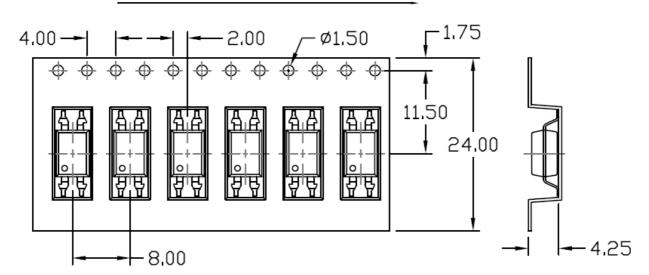
Option SLM(T1)

Input Direction



Option SLM(T2)

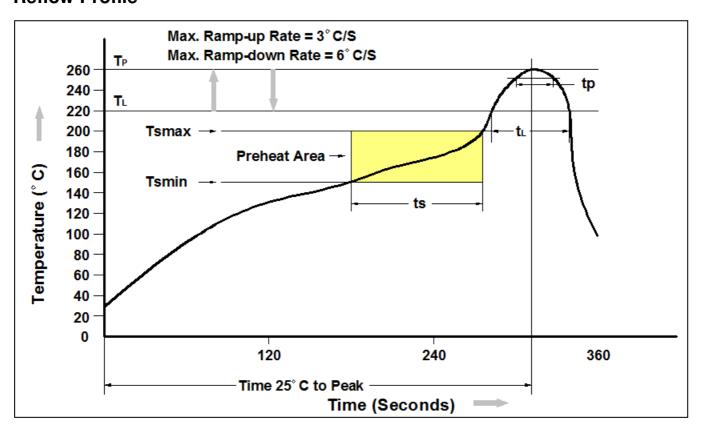
Input Direction







Reflow Profile



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150℃
Temperature Max. (Tsmax)	200℃
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217℃
Time (t _L) Maintained Above (T _L)	60 – 150 seconds
Peak Body Package Temperature	260℃ +0℃ / -5℃
Time (t _P) within 5 °C of 260 °C	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max
Time 25℃ to Peak Temperature	8 minutes max.



DC Low Current Input 4-Pin Phototransistor Optocoupler

DISCLAIMER

CT MICRO RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. CT MICRO DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

DISCOLORATION MIGHT OCCUR ON THE PACKAGE SURFACE AFTER SOLDERING, REFLOW OR LONG TERM USE. THIS DOES NOT IMPACT THE PRODUCT PERFORMANCE NOR THE PRODUCT RELIABILITY.

CT MICRO ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT EXPRESS WRITTEN APPROVAL OF CT MICRO INTERNATIONAL CORPORATION.

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instruction for use provided in the labelling, can be reasonably expected to result in significant injury to the user.
- A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.